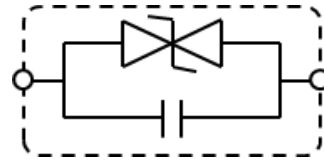


Multilayer Chip Varistor : AVR-M1608C270KTACB

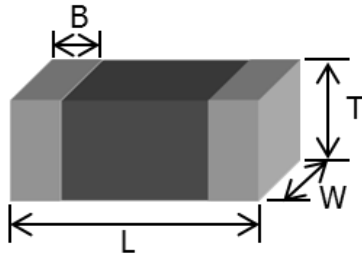
Features

- Automotive (AEC-Q200) grade
- Size : EIA0603 (1.6x0.8mm)
- Excellent ESD clamp characteristics
- High ESD durability : IEC61000-4-2, Contact 25kV
- Operating temperature range : -55°C ~ 150°C

Equivalent Circuit

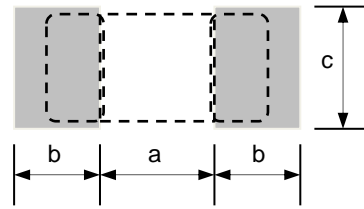


Shapes & Dimensions



Unit / mm				
EIA	L	W	T	B
0603	1.6±0.1	0.8±0.1	0.8±0.1	0.2 Min.

Recommended PCB Pattern



Unit / mm			
EIA	a	b	c
0603	0.6 to 0.8	0.6 to 0.8	0.6 to 0.8

Product Identification

AVR-M 1608 C 270 K T ACB
(1) (2) (3) (4) (5) (6) (7)

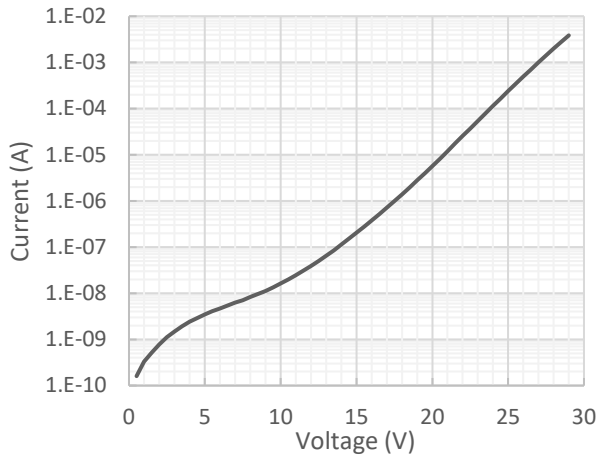
(1)	Series name / AVR-M
(2)	Dimension / 1608:1.6x0.8(mm)
(3)	Structure
(4)	Varistor voltage / 270:27x10 ⁰ (V)
(5)	Varistor voltage tolerance / K : ±10(%)
(6)	Packaging scheme / T : Taping
(7)	TDK internal code

Electrical Characteristics

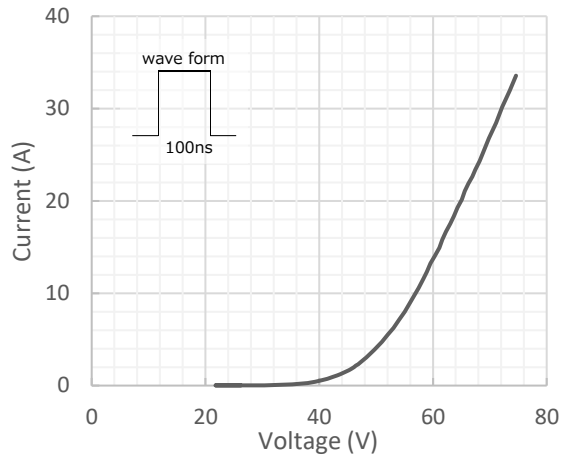
TDK Product Name	Varistor voltage (Breakdown voltage)	Rated voltage	Clamping voltage		Energy	Power Peak Pulse	Peak current	Capacitance
		DC	8/20μs		10/1000μs	10/1000μs	8/20μs	1kHz, 1Vrms
		Max.	Typ.		Max.	Typ.	Max.	Typ.
	V1mA (V)	Vdc	Vcl	Icl	E (Joule)	Ppp (W)	Ip (A)	C (pF)
AVR-M1608C270KTACB	27(24~30)	19	54	2	0.05	45.0	10	60(42 to 78)

Multilayer Chip Varistor : AVR-M1608C270KTACB

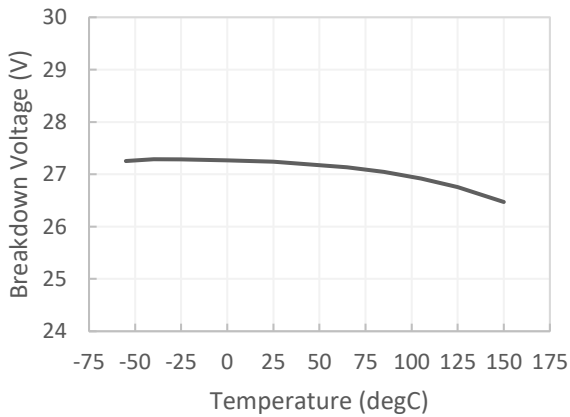
Current - Voltage



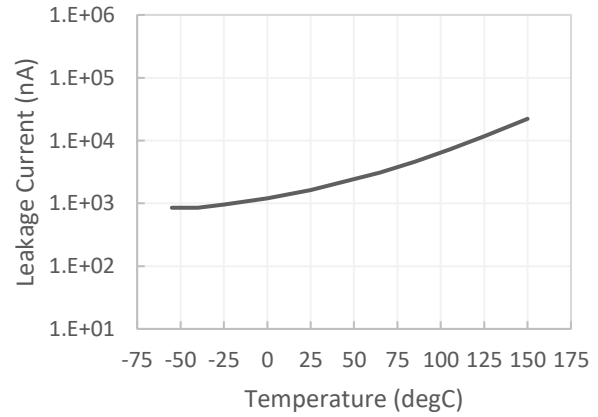
Current - Voltage (TLP)



Breakdown Voltage - Temp.



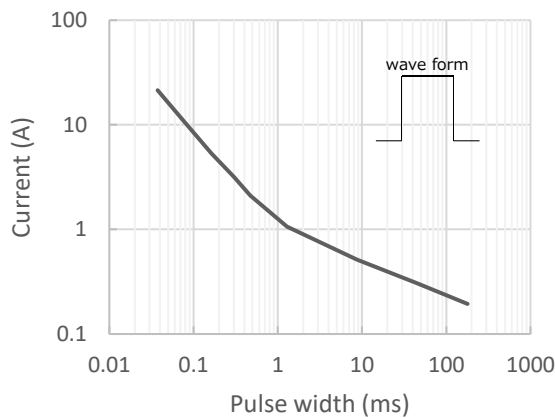
Leakage current - Temp.



※ Voltage : 19 V

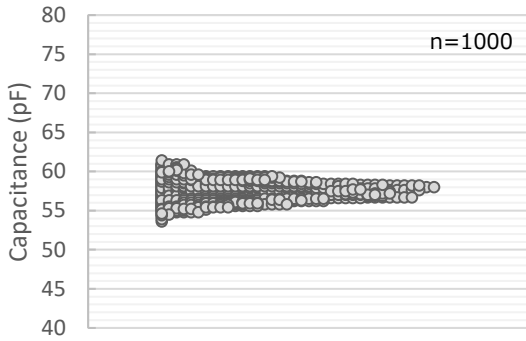
Durability of Pulse Current

(Typ. values)

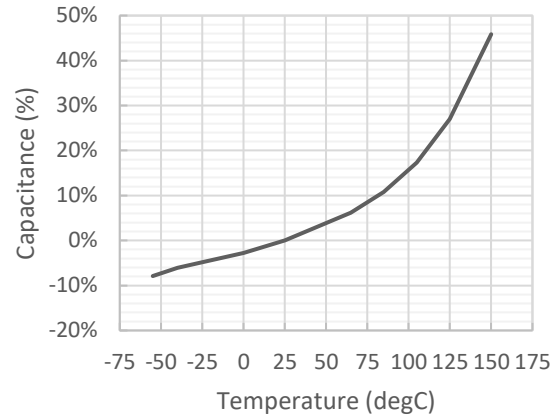


Multilayer Chip Varistor : AVR-M1608C270KTACB

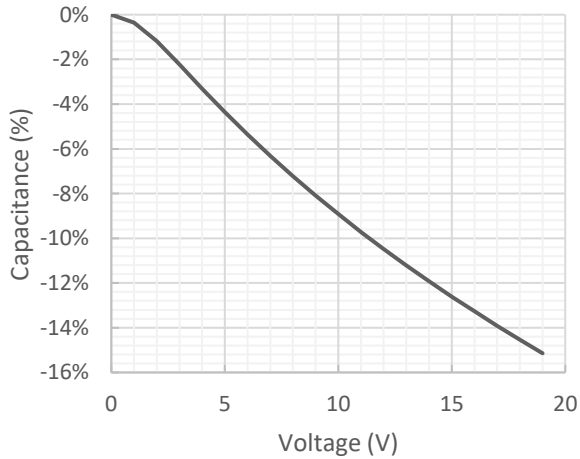
Capacitance Dispersion ※1kHz, 1Vrms



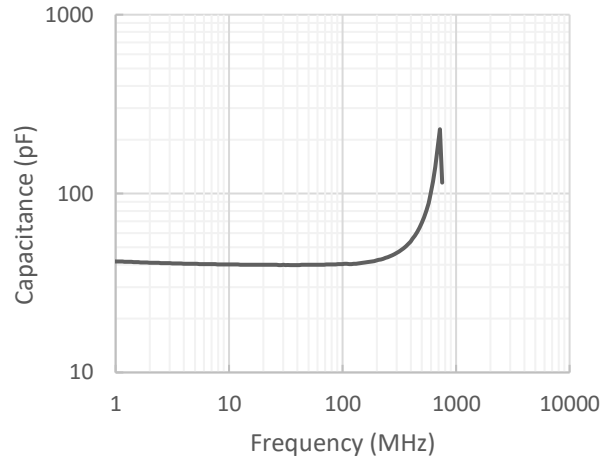
Capacitance - Temp. ※1kHz, 1Vrms



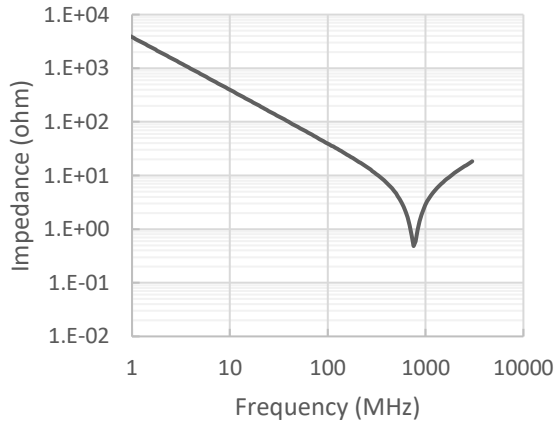
DC bias ※1MHz, 1Vrms



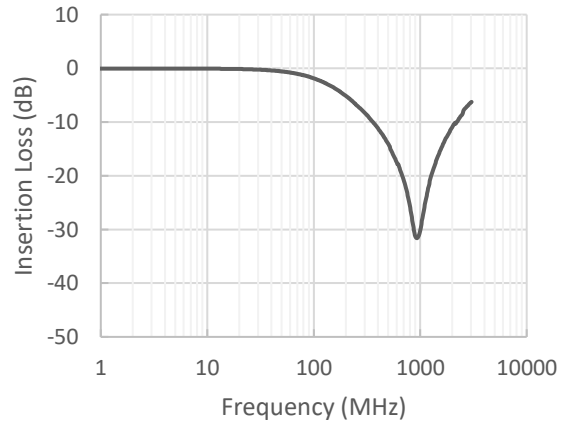
Capacitance - Freq.



Impedance - Freq.



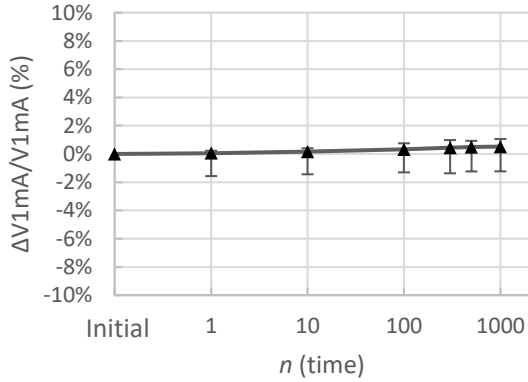
Insertion Loss



Multilayer Chip Varistor : AVR-M1608C270KTACB

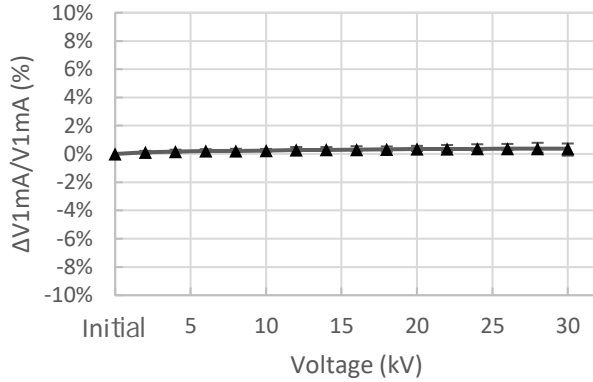
ESD Discharge

▶ 150pF/330ohm, ±25kV, 1000times



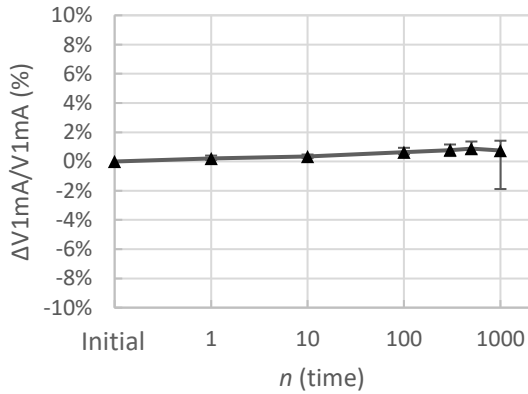
ESD Discharge

▶ 150pF/330ohm, ~±30kV, 10times



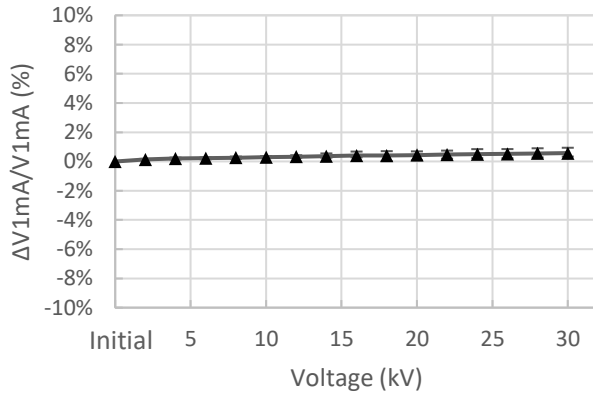
ESD Discharge

▶ 330pF/2000ohm, ±25kV, 1000times



ESD Discharge

▶ 330pF/2000ohm, ~±30kV, 10times



※Criteria : $\Delta V1mA/V1mA \leq 10\%$